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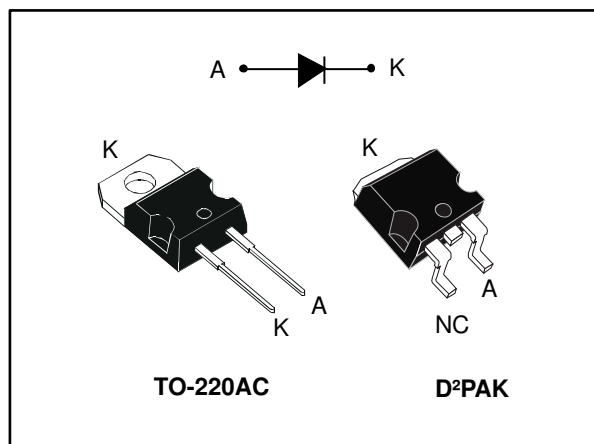
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## Automotive 650 V power Schottky silicon carbide diode

Datasheet - production data



### Description

The SiC diode is an ultra high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode will boost performance in hard switching conditions. Its high forward surge capability ensures good robustness during transient phases.

### Features

- AEC-Q101 qualified
- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability
- PPAP capable
- ECOPACK<sup>®</sup>2 compliant component



Table 1: Device summary

Symbol	Value
$I_{F(AV)}$	10 A
$V_{RRM}$	650 V
$T_j$ (max.)	175 °C

# 1 Characteristics

**Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified)**

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage	T <sub>j</sub> = -40 to +175 °C	650	V
I <sub>F(RMS)</sub>	Forward rms current		22	A
I <sub>F(AV)</sub>	Average forward current	T <sub>c</sub> = 135 °C <sup>(1)</sup> , DC	10	A
I <sub>FRM</sub>	Repetitive peak forward current	T <sub>c</sub> = 135 °C, T <sub>j</sub> = 175 °C, δ = 0.1	41	A
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal, T <sub>c</sub> = 25 °C	90	A
		t <sub>p</sub> = 10 ms sinusoidal, T <sub>c</sub> = 125 °C	80	
		t <sub>p</sub> = 10 μs square, T <sub>c</sub> = 25 °C	470	
T <sub>stg</sub>	Storage temperature range		-55 to +175	°C
T <sub>j</sub>	Operating junction temperature <sup>(2)</sup>		-40 to +175	°C

**Notes:**

<sup>(1)</sup>Value based on R<sub>th(j-c)</sub> max.

<sup>(2)</sup>(dP<sub>tot</sub>/dT<sub>j</sub>) < (1/R<sub>th(j-a)</sub>) condition to avoid thermal runaway for a diode on its own heatsink.

**Table 3: Thermal parameters**

Symbol	Parameter	Value		Unit
		Typ.	Max.	
R <sub>th(j-c)</sub>	Junction to case	1.25	1.5	°C/W

**Table 4: Static electrical characteristics**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>	-	9	100	μA
		T <sub>j</sub> = 150 °C		-	85	425	
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10 A	-	1.56	1.75	V
		T <sub>j</sub> = 150 °C		-	1.98	2.5	

**Notes:**

<sup>(1)</sup>Pulse test: t<sub>p</sub> = 10 ms, δ < 2%

<sup>(2)</sup>Pulse test: t<sub>p</sub> = 500 μs, δ < 2%

To evaluate the conduction losses, use the following equation:

$$P = 1.35 \times I_{F(AV)} + 0.115 \times I_{F(RMS)}^2$$

Table 5: Dynamic electrical characteristics

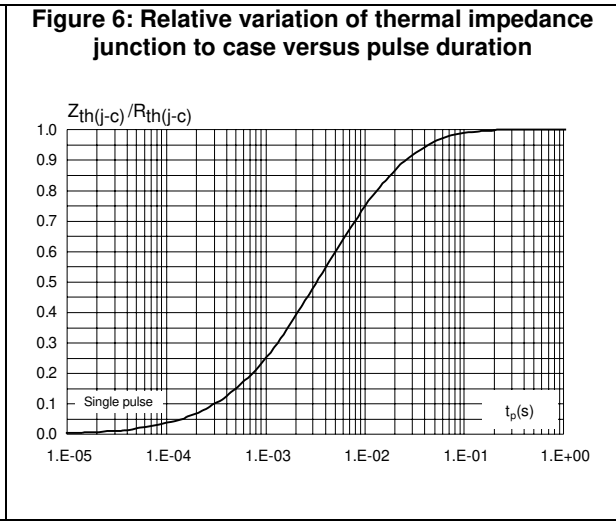
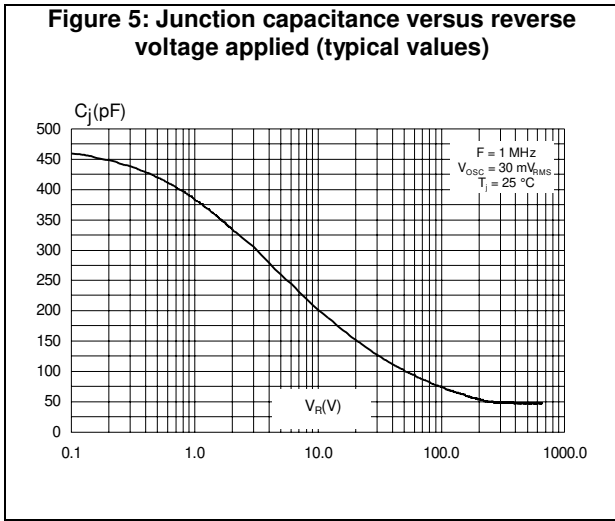
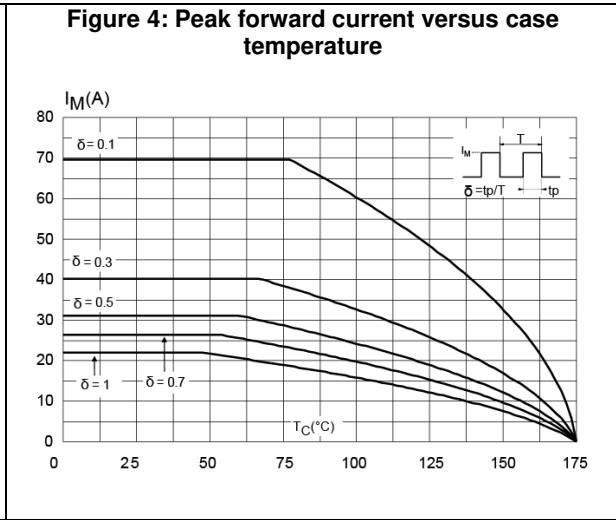
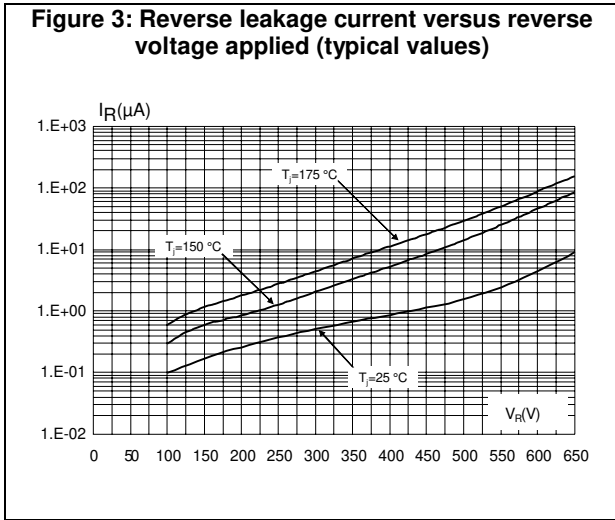
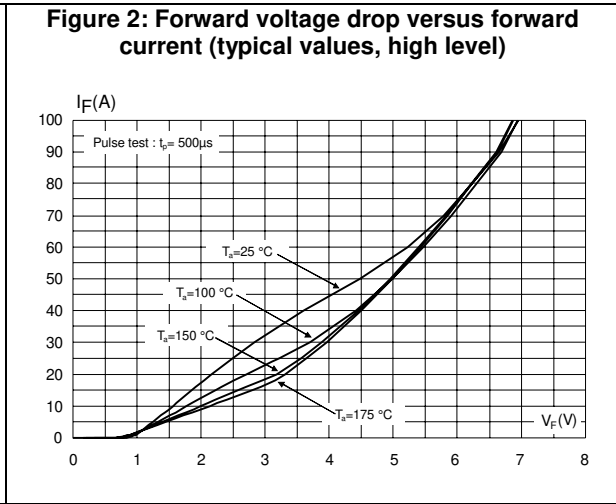
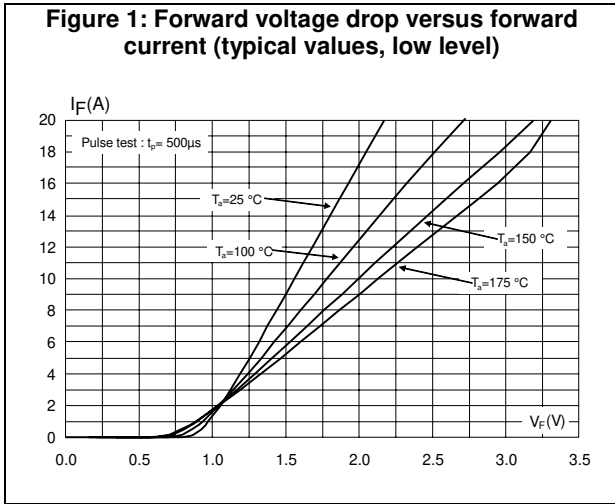
Symbol	Parameter	Test conditions	Typ.	Unit
$Q_{Cj}^{(1)}$	Total capacitive charge	$V_R = 400 \text{ V}$	28.5	nC
$C_j$	Total capacitance	$V_R = 0 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	480	pF
		$V_R = 400 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	48	

**Notes:**

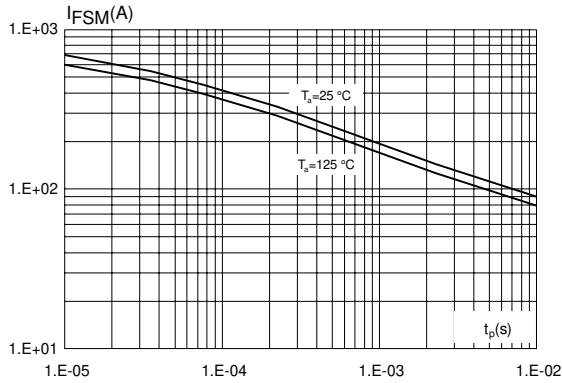
<sup>(1)</sup>Most accurate value for the capacitive charge:  $Q_{Cj} = \int_0^{V_{OUT}} C_j(V_R) \cdot dV_R$



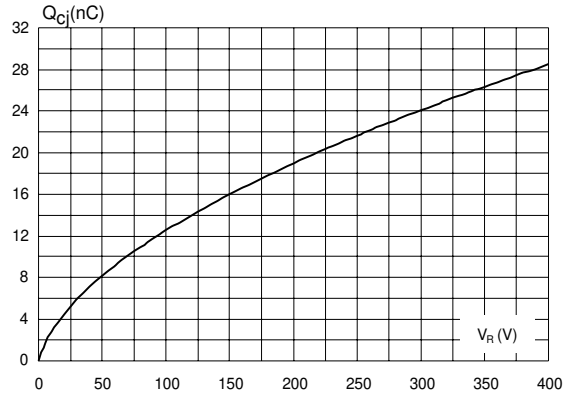
# 1.1 Characteristics (curves)



**Figure 7: Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)**



**Figure 8: Total capacitive charges versus reverse voltage applied (typical values)**



**Figure 9: Thermal resistance junction to ambient versus copper surface under tab for D<sup>2</sup>PAK package (typical values)**

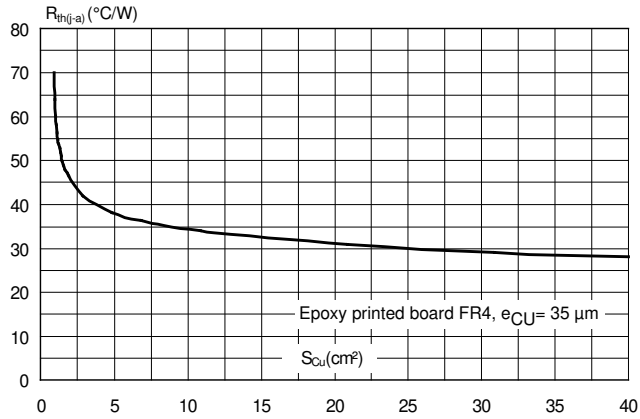
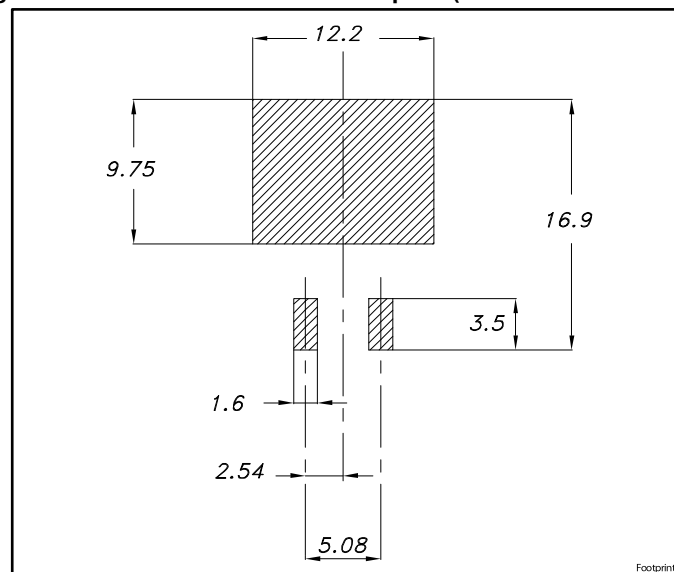




Table 6: D<sup>2</sup>PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10		10.40	0.394		0.409
E1	8.50	8.70	8.90	0.335	0.343	0.346
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.4			0.015	
V2	0°		8°	0°		8°

Figure 11: D<sup>2</sup>PAK recommended footprint (dimensions are in mm)



## 2.2 TO-220AC package information

Figure 12: TO-220AC package outline

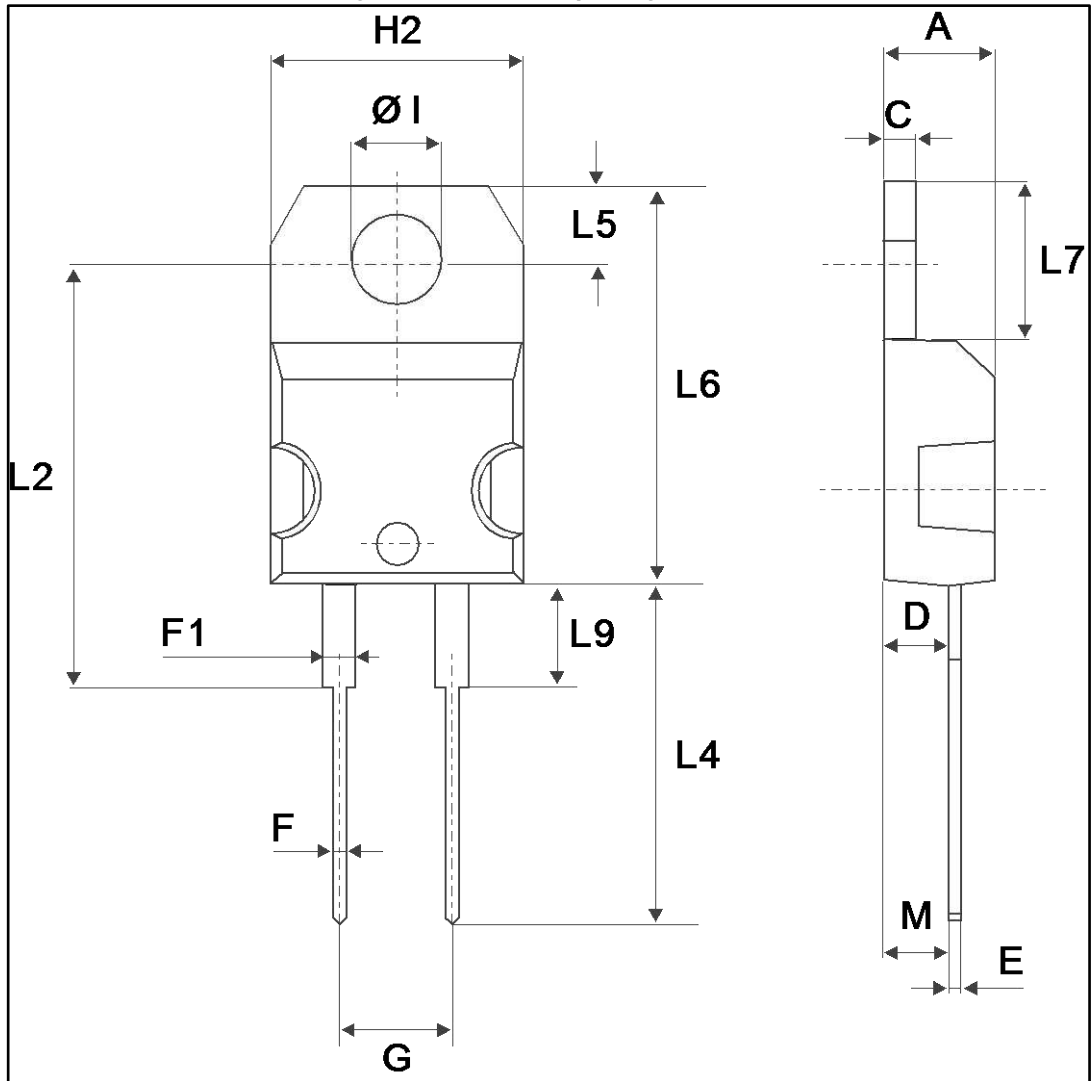


Table 7: TO-220AC package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam	3.75	3.85	0.147	0.151

### 3 Ordering information

Table 8: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC10H065GY-TR	PSC10H065GY	D <sup>2</sup> PAK	1.48 g	1000	Tape and reel
STPSC10H065DY	PSC10H065DY	TO-220AC	1.86 g	50	Tube

### 4 Revision history

Table 9: Document revision history

Date	Revision	Changes
26-Jun-2014	1	First issue.
19-Sep-2014	2	Updated <i>Table 8</i> .
24-Sep-2015	3	Added device in D2PAK. Updated the entire document accordingly.
06-Feb-2017	4	Updated D <sup>2</sup> PAK package information section.

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